

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 4, line 28 with the following amended paragraph:

That is, the CMP slurry composition for oxide film of the present invention includes the HXO_n compound, and thus the polishing selectivity ratio of for a nitride hard mask film to an interlayer insulating film formed of an oxide film ~~to a nitride hard mask film~~ is ranges from 1:1 to 1:3, preferably from 1:1 to 1:2, ~~and the polishing selectivity ratio of the oxide film to the silicon layer is 1:3, preferably 1:2.~~

Please replace the paragraph beginning on page 6, line 7 with the following amended paragraph:

A word line pattern 114 having a hard mask pattern 113 on a conductive layer pattern 2 112 for word line is formed by sequentially etching the hard mask film and the conductive layer for word line.

Please replace the paragraph beginning on page 6, line 29 with the following amended paragraph:

The etching process is performed by a self-aligned contact (SAC) process using C_4F_8 , C_2F_6 or C_3F_8 source having a high ~~polishing~~ etching selectivity ratio to the nitride film, preferably C_4F_8 source.